

Docket No. 250490US2/ams



IRW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yukio TANIGUCHI, et al.

SERIAL NO: 10/802,836

GAU:

FILED: March 18, 2004

EXAMINER:

FOR: METHOD AND APPARATUS FOR FORMING CRYSTALLINE PORTIONS OF SEMICONDUCTOR FILM

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

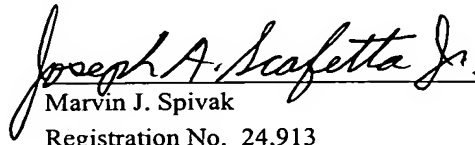
- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.

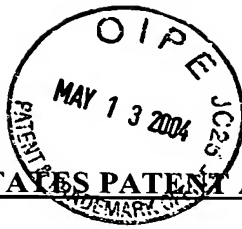

Marvin J. Spivak
Registration No. 24,913

Joseph A. Scafetta, Jr.
Registration No. 26, 803

Customer Number

22850

Tel. (703) 413-3000
Fax. (703) 413-2220
(OSMMN 05/03)



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Yukio TANIGUCHI, et al.

SERIAL NO: 10/802,836

GROUP:

FILED: March 18, 2004

EXAMINER:

FOR: METHOD AND APPARATUS FOR FORMING CRYSTALLINE PORTIONS
OF SEMICONDUCTOR FILM

STATEMENT OF RELEVANCY

Reference AV on Form PTO-1449:

Please see Fig. 3 and its description.

Reference AW on Form PTO-1449:

Please see Fig. 2 and its description.

Reference AX on Form PTO-1449:

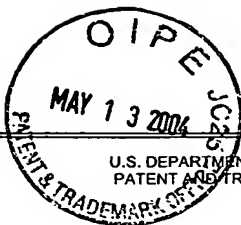
Please see Fig. 2 and its description.

Reference AY on Form PTO-1449:

Please see the ninth slide.

Reference AZ on Form PTO-1449:

This reference is discussed in the specification.



Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 250490US2		SERIAL NO. 10/802,836	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Yukio TANIGUCHI, et al.			
				FILING DATE March 18, 2004		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AV	Chang-Ho OH, et al., Japan Journal of Applied Physics, vol. 37, pages L492-L495, "A NOVEL PHASE-MODULATED EXCIMER-LASER CRYSTALLIZATION METHOD OF SILICON THIN FILMS", May 1, 1998					
	AW	M. NAKATA, et al., The Japan Society of Applied Physics, vol. 40, part 1, no. 5, pages 3049-3054, "A NEW NUCLEATION-SITE-CONTROL EXCIMER-LASER-CRYSTALLIZATION METHOD", May 2001					
	AX	M. MATSUMURA, IDW '02 AMD5-1, pages 263-266, "ADVANCED LASER-CRYSTALLIZATION TECHNOLOGIES OF Si FOR HIGH-PERFORMANCE TFTs", 2001					
	AY	International Display Workshops, pages 1-6, "ADVANCED LASER-CRYSTALLIZATION TECHNOLOGIES OF Si FOR HIGH-PERFORMANCES TFTs" (with partial English translation)					
	AZ	Journal of The Surface Science Society of Japan, vol. 21, no. 5, pages 278-287, "PREPARATION OF ULTRA-LARGE GRAIN SILICON THIN-FILMS BY EXCIMER-LASER", 2000 (with partial English translation)					
					<input type="checkbox"/> Additional References sheet(s) attached		
Examiner					Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							